# CSD17575Q3 30-V N-Channel NexFET™ Power MOSFET

## 1 Features

- Low $Q_g$ and $Q_{gd}$
- Low $R_{DS(on)}$
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 3.3 mm × 3.3 mm Plastic Package

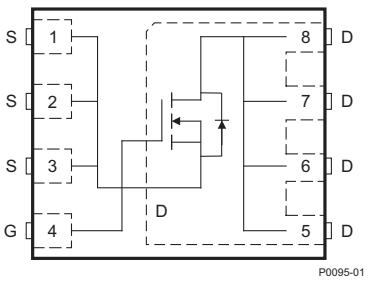
## 2 Applications

- Point of Load Synchronous Buck Converter for Applications in Networking, Telecom, and Computing Systems
- Optimized for Synchronous FET Applications

## 3 Description

This 1.9 mΩ, 30 V, SON 3×3 NexFET™ power MOSFET is designed to minimize losses in power conversion applications.

**Top View**




**Product Summary**

| $T_A$ = 25°C | | TYPICAL VALUE | | UNIT |
|---|---|---|---|---|
| $V_{DS}$ | Drain-to-Source Voltage | 30 | | V |
| $Q_g$ | Gate Charge Total (4.5V) | 23 | | nC |
| $Q_{gd}$ | Gate Charge Gate-to-Drain | 5.4 | | nC |
| $R_{DS(on)}$ | Drain-to-Source On-Resistance | $V_{GS}$ = 4.5 V | 2.6 | mΩ |
| | | $V_{GS}$ = 10 V | 1.9 | |
| $V_{th}$ | Threshold Voltage | 1.4 | | V |

**Ordering Information**[1]

| Device | Media | Qty | Package | Ship |
|---|---|---|---|---|
| CSD17575Q3 | 13-Inch Reel | 2500 | SON 3.3 × 3.3 mm Plastic Package | Tape and Reel |
| CSD17575Q3T | 13-Inch Reel | 250 | | |

(1) For all available packages, see the orderable addendum at the end of the data sheet.

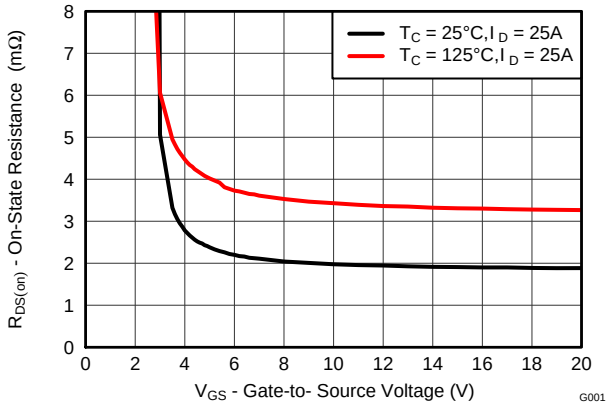
**Absolute Maximum Ratings**

| $T_A$ = 25°C | | VALUE | UNIT |
|---|---|---|---|
| $V_{DS}$ | Drain-to-Source Voltage | 30 | V |
| $V_{GS}$ | Gate-to-Source Voltage | ±20 | V |
| $I_D$ | Continuous Drain Current (Package Limit) | 60 | A |
| | Continuous Drain Current (Silicon Limit), $T_C$ = 25°C | 182 | |
| | Continuous Drain Current[1] | 27 | |
| $I_{DM}$ | Pulsed Drain Current[2] | 240 | A |
| $P_D$ | Power Dissipation[1] | 2.8 | W |
| | Power Dissipation, $T_C$ = 25°C | 108 | |
| $T_J$, $T_{stg}$ | Operating Junction and Storage Temperature Range | –55 to 150 | °C |
| $E_{AS}$ | Avalanche Energy, single pulse $I_D$ = 48, L = 0.1 mH, $R_G$ = 25 Ω | 115 | mJ |

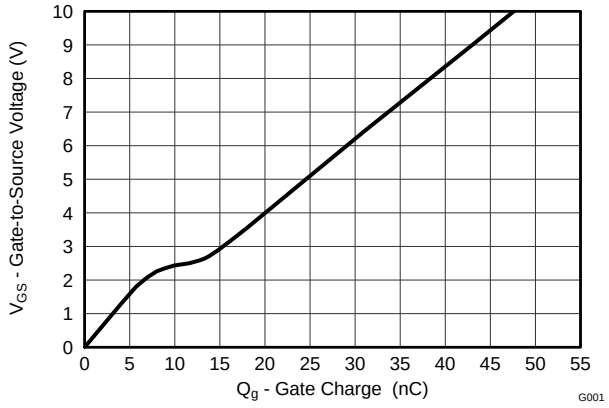
(1) Typical $R_{\theta JA}$ = 45°C/W on 1-inch$^2$ Cu (2 oz.) on 0.060-inch thick FR4 PCB.

(2) Max $R_{\theta JC}$ = 1.5°C/W, pulse duration ≤100 µs, duty cycle ≤1%

**$R_{DS(on)}$ vs $V_{GS}$**




**Gate Charge**




An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.

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## 4 Revision History

**Changes from Original (June 2014) to Revision A** **Page**

- Added b1, d, d1, and K dimensions to the mechanical information table ... 8


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# 5 Specifications

## 5.1 Electrical Characteristics

($T_A$ = 25°C unless otherwise stated)

| PARAMETER | | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|
| **STATIC CHARACTERISTICS** | | | | | | |
| $BV_{DSS}$ | Drain-to-Source Voltage | $V_{GS}$ = 0 V, $I_D$ = 250 µA | 30 | | | V |
| $I_{DSS}$ | Drain-to-Source Leakage Current | $V_{GS}$ = 0 V, $V_{DS}$ = 24 V | | | 1 | µA |
| $I_{GSS}$ | Gate-to-Source Leakage Current | $V_{DS}$ = 0 V, $V_{GS}$ = ±20 V | | | 100 | nA |
| $V_{GS(th)}$ | Gate-to-Source Threshold Voltage | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 µA | 1.1 | 1.4 | 1.8 | V |
| $R_{DS(on)}$ | Drain-to-Source On-Resistance | $V_{GS}$ = 4.5 V, $I_D$ = 25 A | | 2.6 | 3.2 | mΩ |
| | | $V_{GS}$ = 10 V, $I_D$ = 25 A | | 1.9 | 2.3 | |
| $g_{fs}$ | Transconductance | $V_{DS}$ = 3 V, $I_D$ = 25 A | | 118 | | S |
| **DYNAMIC CHARACTERISTICS** | | | | | | |
| $C_{ISS}$ | Input Capacitance | $V_{GS}$ = 0 V, $V_{DS}$ = 15 V, $f$ = 1 MHz | | 3400 | 4420 | pF |
| $C_{OSS}$ | Output Capacitance | | | 393 | 511 | pF |
| $C_{RSS}$ | Reverse Transfer Capacitance | | | 157 | 204 | pF |
| $R_g$ | Series Gate Resistance | | | 0.9 | 1.8 | Ω |
| $Q_g$ | Gate Charge Total (4.5 V) | $V_{DS}$ = 15 V, $I_D$ = 25 A | | 23 | 30 | nC |
| $Q_{gd}$ | Gate Charge Gate-to-Drain | | | 5.4 | | nC |
| $Q_{gs}$ | Gate Charge Gate-to-Source | | | 8.5 | | nC |
| $Q_{g(th)}$ | Gate Charge at $V_{th}$ | | | 4.6 | | nC |
| $Q_{OSS}$ | Output Charge | $V_{DS}$ = 15 V, $V_{GS}$ = 0 V | | 11.6 | | nC |
| $t_{d(on)}$ | Turn On Delay Time | $V_{DS}$ = 15 V, $V_{GS}$ = 4.5 V $I_D$ = 25 A $R_G$ = 2 Ω | | 4 | | ns |
| $t_r$ | Rise Time | | | 10 | | ns |
| $t_{d(off)}$ | Turn Off Delay Time | | | 20 | | ns |
| $t_f$ | Fall Time | | | 3 | | ns |
| **DIODE CHARACTERISTICS** | | | | | | |
| $V_{SD}$ | Diode Forward Voltage | $I_S$ = 25 A, $V_{GS}$ = 0 V | | 0.8 | 1 | V |
| $Q_{rr}$ | Reverse Recovery Charge | $V_{DD}$ = 15 V, $I_F$ = 25 A, di/dt = 300 A/µs | | 15 | | nC |
| $t_{rr}$ | Reverse Recovery Time | | | 13 | | ns |

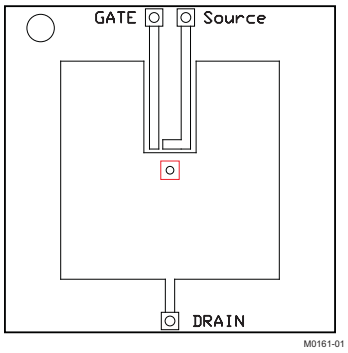
## 5.2 Thermal Information

($T_A$ = 25°C unless otherwise stated)

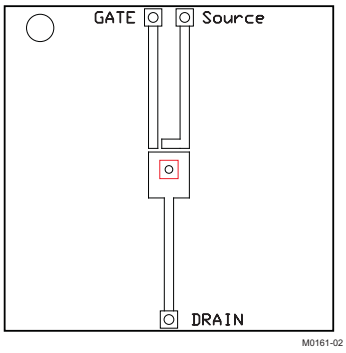
| THERMAL METRIC | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction-to-Case Thermal Resistance(1) | | | 1.5 | °C/W |
| $R_{\theta JA}$ | Junction-to-Ambient Thermal Resistance(1)(2) | | | 55 | |

(1) $R_{\theta JC}$ is determined with the device mounted on a 1-inch$^2$ (6.45-cm$^2$), Cu pad on a 1.5-inches × 1.5-inches thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas RθJA is determined by the user's board design.
(2) Device mounted on FR4 material with 1-inch$^2$ 2-oz.Cu.

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Max $R_{\theta JA}$ = 55°C/W when mounted on 1 inch$^2$ of 2 oz. Cu.




Max $R_{\theta JA}$ = 160°C/W when mounted on minimum pad area of 2 oz. Cu.

## 5.3 Typical MOSFET Characteristics

($T_A$ = 25°C unless otherwise stated)

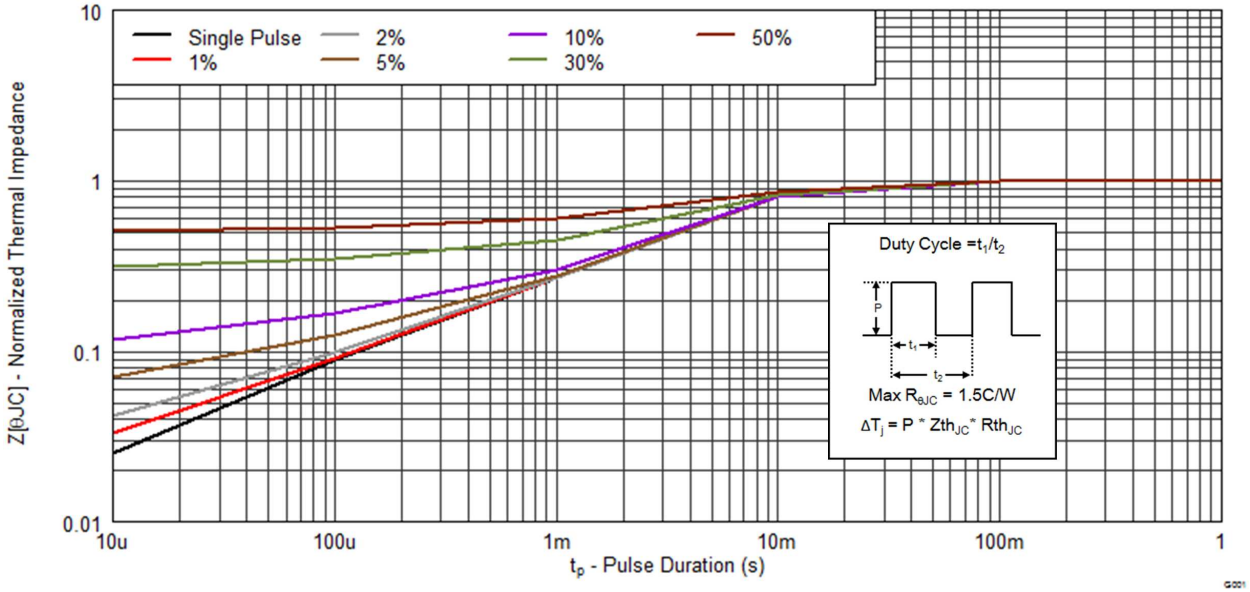



**Figure 1. Transient Thermal Impedance**


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## Typical MOSFET Characteristics (continued)

($T_A$ = 25°C unless otherwise stated)

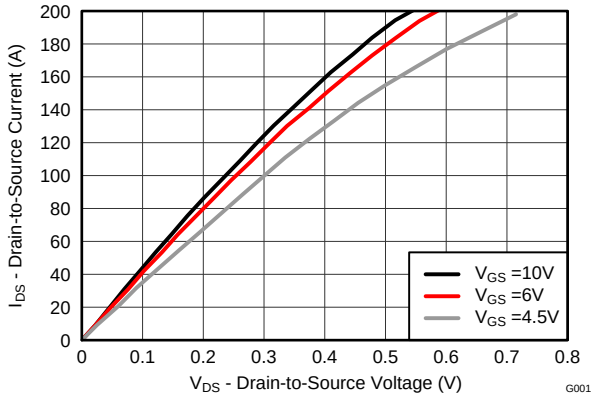



**Figure 2. Saturation Characteristics**

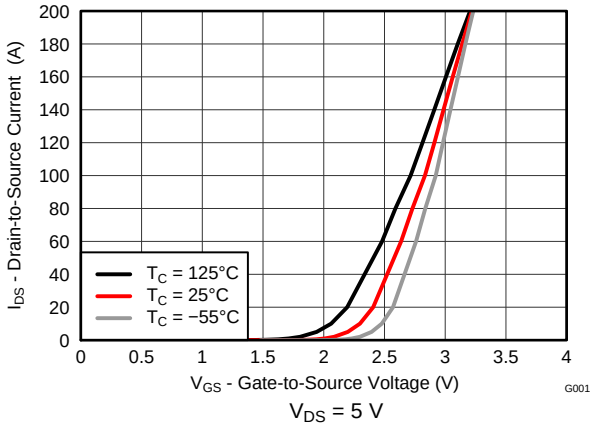



**Figure 3. Transfer Characteristics**

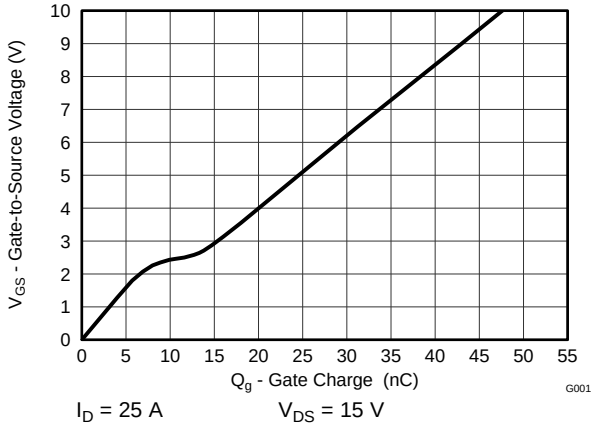



**Figure 4. Gate Charge**

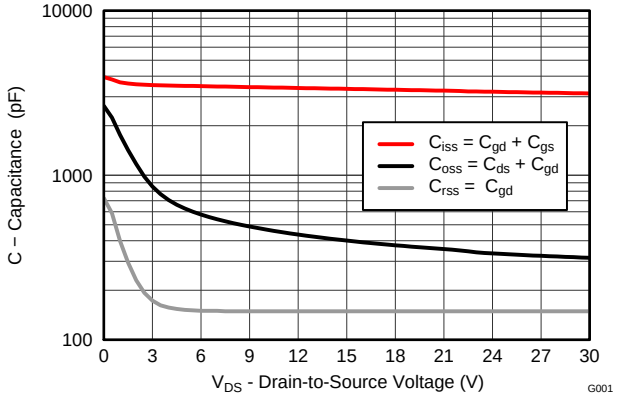



**Figure 5. Capacitance**

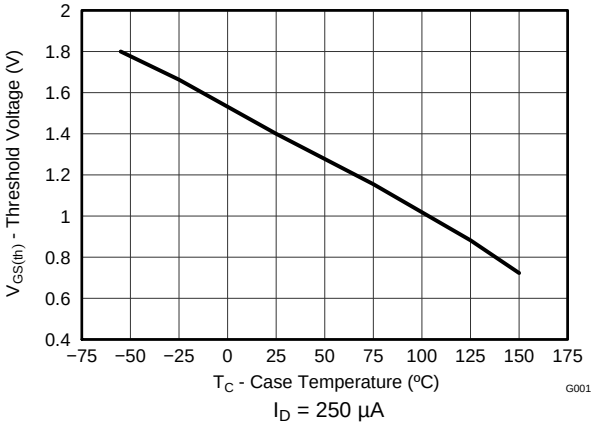



**Figure 6. Threshold Voltage vs Temperature**

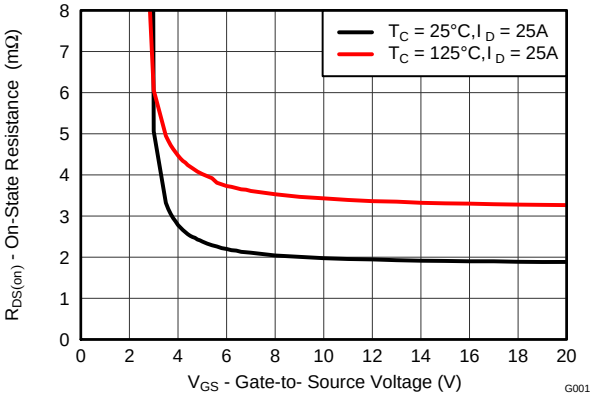



**Figure 7. On-State Resistance vs Gate-to-Source Voltage**

## Typical MOSFET Characteristics (continued)

($T_A$ = 25°C unless otherwise stated)

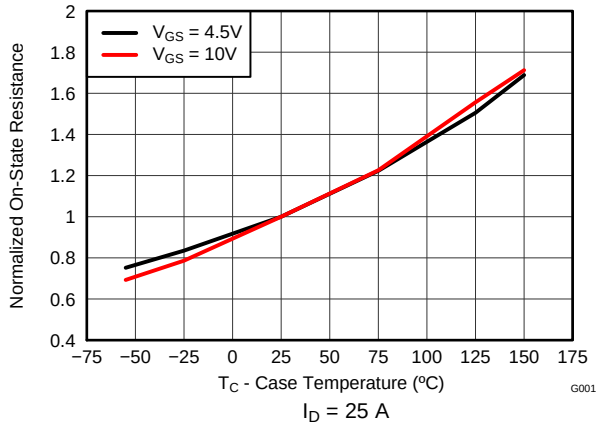



**Figure 8. Normalized On-State Resistance vs Temperature**

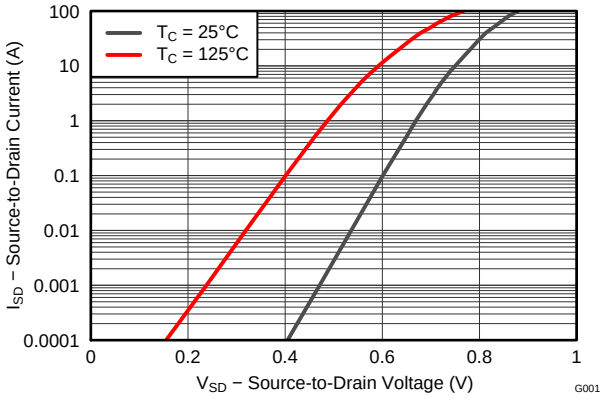



**Figure 9. Typical Diode Forward Voltage**

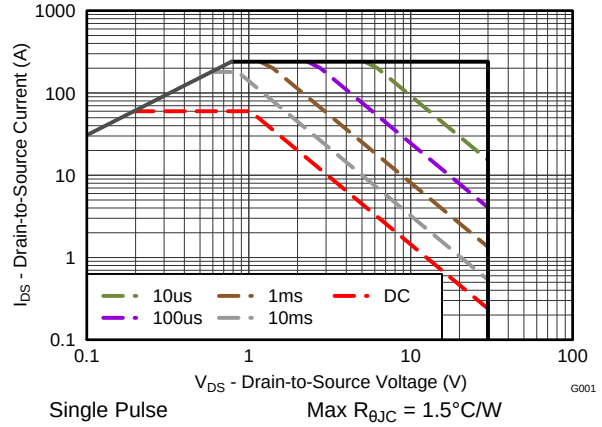



**Figure 10. Maximum Safe Operating Area**

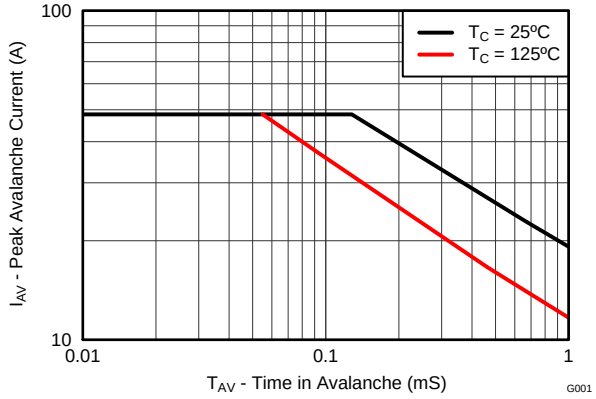



**Figure 11. Single Pulse Unclamped Inductive Switching**

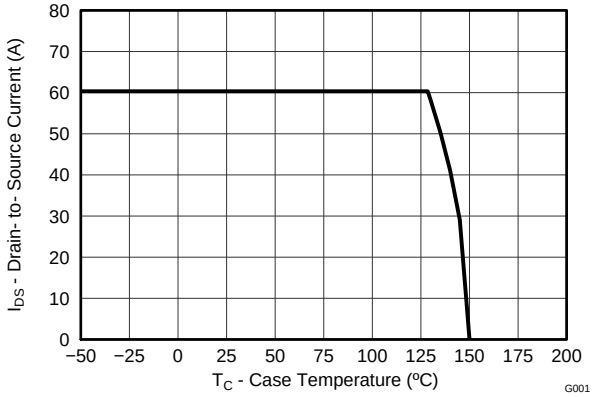



**Figure 12. Maximum Drain Current vs Temperature**


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# 6 Device and Documentation Support

## 6.1 Trademarks

NexFET is a trademark of Texas Instruments.

## 6.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## 6.3 Glossary

SLYZ022 — *TI Glossary*.

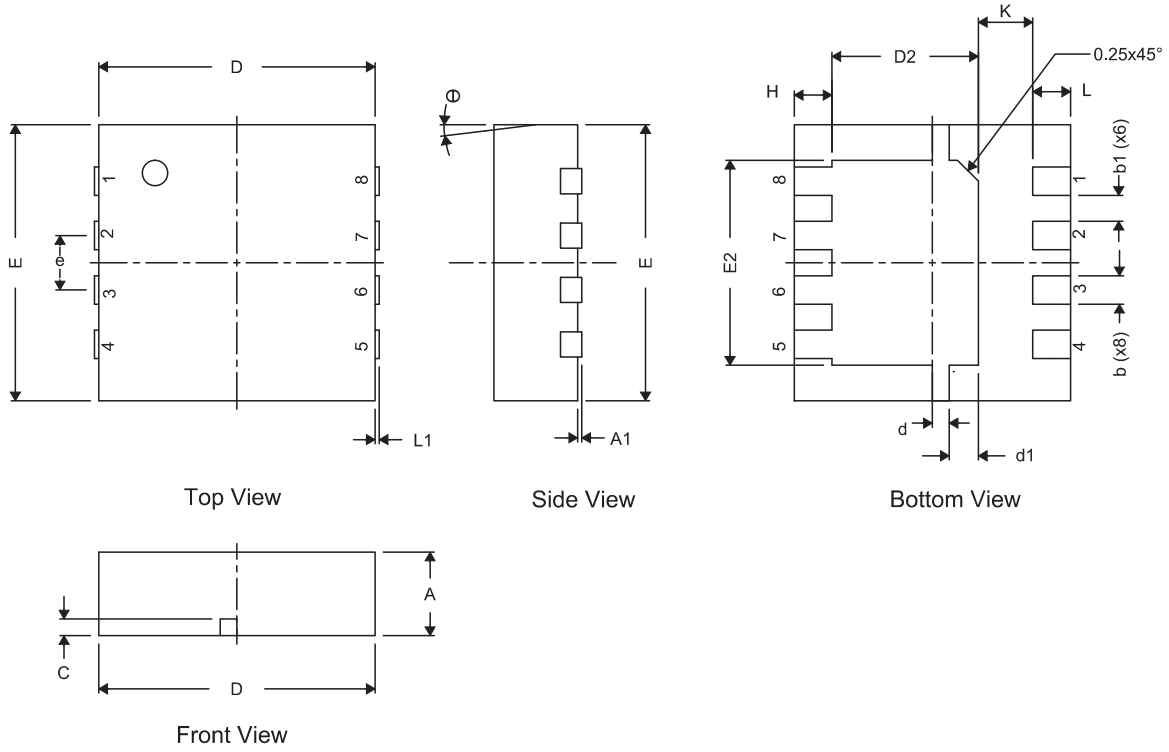
This glossary lists and explains terms, acronyms, and definitions.

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# 7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

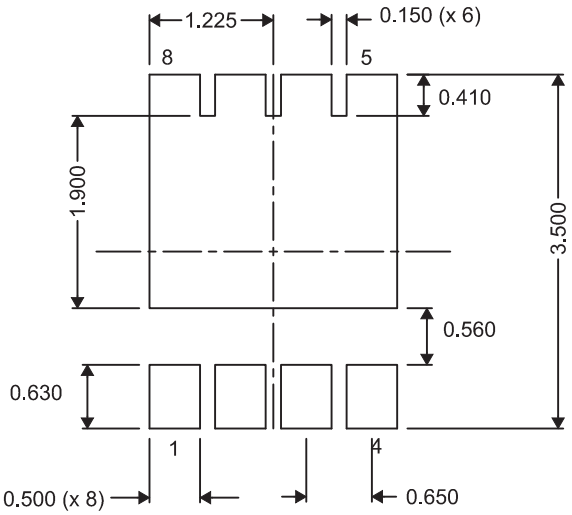
## 7.1 Q3 Package Dimensions




| DIM | MILLIMETERS | | | INCHES | | |
|---|---|---|---|---|---|---|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.950 | 1.000 | 1.100 | 0.037 | 0.039 | 0.043 |
| A1 | 0.000 | 0.000 | 0.050 | 0.000 | 0.000 | 0.002 |
| b | 0.280 | 0.340 | 0.400 | 0.011 | 0.013 | 0.016 |
| b1 | | 0.310 NOM | | | 0.012 NOM | |
| c | 0.150 | 0.200 | 0.250 | 0.006 | 0.008 | 0.010 |
| D | 3.200 | 3.300 | 3.400 | 0.126 | 0.130 | 0.134 |
| D2 | 1.650 | 1.750 | 1.800 | 0.065 | 0.069 | 0.071 |
| d | 0.150 | 0.200 | 0.250 | 0.006 | 0.008 | 0.010 |
| d1 | 0.300 | 0.350 | 0.400 | 0.012 | 0.014 | 0.016 |
| E | 3.200 | 3.300 | 3.400 | 0.126 | 0.130 | 0.134 |
| E2 | 2.350 | 2.450 | 2.550 | 0.093 | 0.096 | 0.100 |
| e | | 0.650 TYP | | | 0.026 | |
| H | 0.35 | 0.450 | 0.550 | 0.014 | 0.018 | 0.022 |
| K | | 0.650 TYP | | | 0.026 TYP | |
| L | 0.35 | 0.450 | 0.550 | 0.014 | 0.018 | 0.022 |
| L1 | 0 | — | 0 | 0 | — | 0 |
| θ | 0 | — | 0 | 0 | — | 0 |

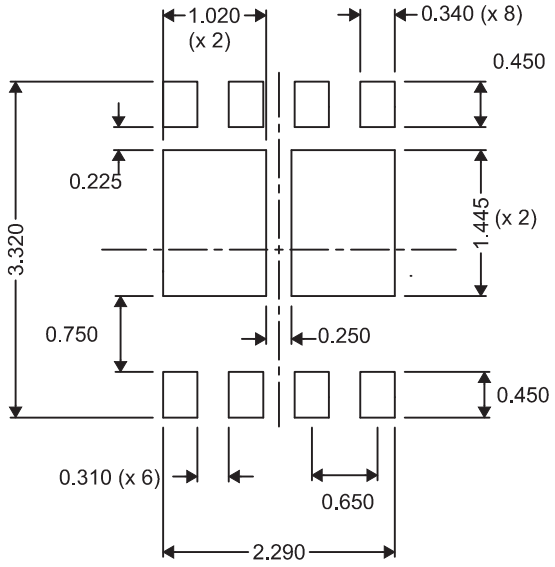

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## 7.2 Recommended PCB Pattern



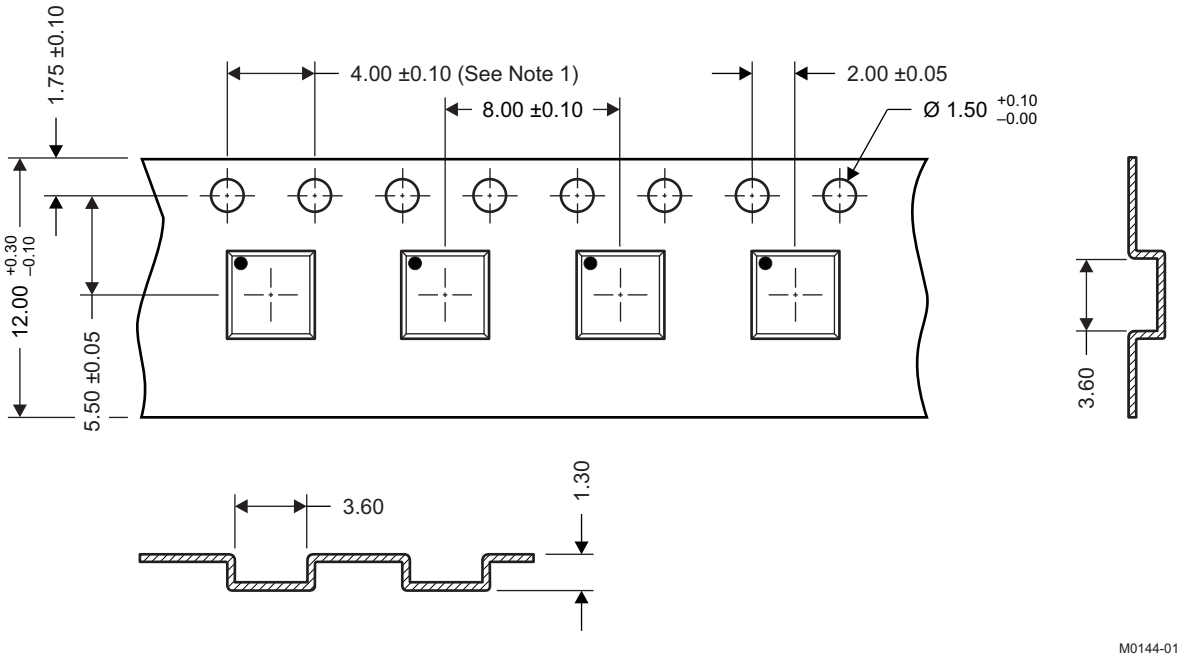

For recommended circuit layout for PCB designs, see application note SLPA005 – *Reducing Ringing Through PCB Layout Techniques*.

## 7.3 Recommended Stencil Opening




All dimensions are in mm, unless otherwise specified.

## 7.4 Q3 Tape and Reel Information




**Notes:**

1. 10 sprocket hole pitch cumulative tolerance ±0.2
2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm
3. Material: black static dissipative polystyrene
4. All dimensions are in mm (unless otherwise specified).
5. Thickness: 0.30 ±0.05 mm
6. MSL1 260°C (IR and Convection) PbF Reflow Compatible


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## PACKAGING INFORMATION

| Orderable Device | Status (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan (2) | Lead/Ball Finish (6) | MSL Peak Temp (3) | Op Temp (°C) | Device Marking (4/5) | Samples |
|---|---|---|---|---|---|---|---|---|---|---|---|
| CSD17575Q3 | ACTIVE | VSON-CLIP | DQG | 8 | 2500 | Green (RoHS & no Sb/Br) | SN | Level-1-260C-UNLIM | | CSD17575 | Samples |
| CSD17575Q3T | ACTIVE | VSON-CLIP | DQG | 8 | 250 | Green (RoHS & no Sb/Br) | SN | Level-1-260C-UNLIM | -55 to 150 | CSD17575 | Samples |

(1) The marketing status values are defined as follows:
**ACTIVE:** Product device recommended for new designs.
**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.
**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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